HARRIS

CD4008B Types

CMOS 4-Bit Full Adder

With Parallel Carry Out

High-Voltage Types (20-Volt Rating)

■ CD4008B types consist of four full adder stages with fast look ahead carry provision from stage to stage. Circuitry is included to provide a fast "parallel-carry-out" but to permit high-speed operation in arithmetic sections using several CD4008B's.

CD4008B inputs include the four sets of bits to be added, A_1 to A_4 and B_1 to B_4, in addition to the "Carry In" bit from a previous section. CD4008B outputs include the four sum bits, S_1 to S_4. In addition to the high speed "parallel-carry-out" which may be utilized at a succeeding CD4008B section.

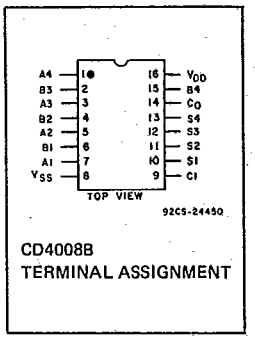
The CD4008B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

- 4 sum outputs plus parallel look-ahead carry-output
- High-speed operation — sum in-to-sum out, 160 ns typ; carry in-to-carry out, 50 ns typ. at V_{DD} = 10 V, C_L = 50 pF
- Standardized, symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package temperature range): 1 V at V_{DD} = 5 V; 2 V at V_{DD} = 10 V; 2.5 V at V_{DD} = 15 V
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative **Standard No. 13B, "Standard Specifications** for Description of 'B' Series CMOS Devices"

Applications:

- Binary addition/arithmetic units



CD4008B
TERMINAL ASSIGNMENT

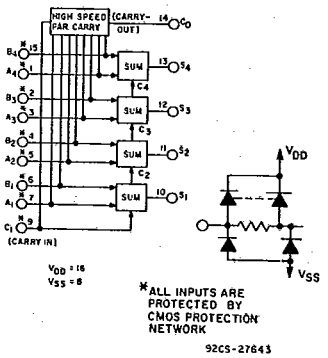


Fig. 1 — CD4008B logic diagram.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
								+25			
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	5	5	150	150	–	0.04	5	μA
	–	0,10	10	10	10	300	300	–	0.04	10	
	–	0,15	15	20	20	600	600	–	0.04	20	
	–	0,20	20	100	100	3000	3000	–	0.08	100	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	0.5, 4.5	–	5	1.5				—	—	1.5	V
	1, 9	–	10	3				—	—	3	
	1.5,13.5	–	15	4				—	—	4	
Input High Voltage, V_{IH} Min.	0.5, 4.5	–	5	3.5				3.5	—	—	
	1, 9	–	10	7				7	—	—	
	1.5,13.5	-	15	11				11	—	—	
Input Current I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

TRUTH TABLE

A_i	B_i	C_i	C_0	SUM
0	0	0	0	0
1	0	0	0	1
0	1	0	0	1
1	1	0	1	0
0	0	1	0	1
1	0	1	1	0
0	1	1	1	0
1	1	1	1	1

RECOMMENDED OPERATING CONDITIONS *at T_A = 25°C, Except as Noted. For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:*

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A = Full Package Temperature Range)	3	18	V

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
Voltages referenced to V_{SS} Terminal) ..... -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C ..... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mW
OPERATING-TEMPERATURE RANGE (T_A) ..... -55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

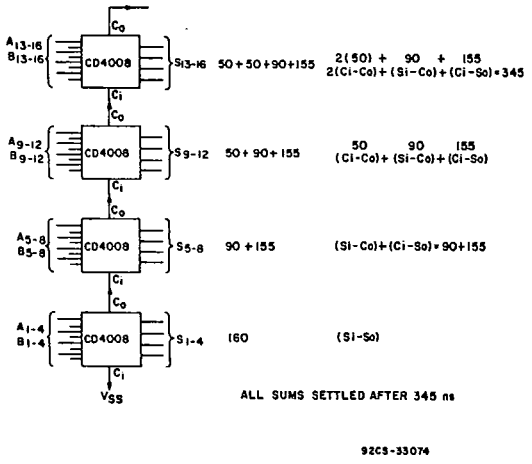


Fig.2 – Typical propagation delay for a 16-bit adder (10 V operation).

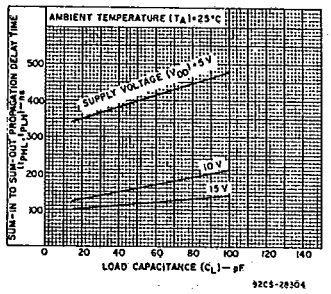


Fig.3 – Typical sum-in to sum-out propagation delay time vs. load capacitance.

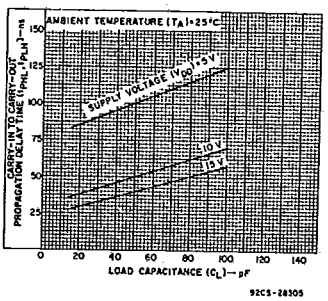


Fig.4 – Typical carry-in to carry-out propagation delay time vs. load capacitance.

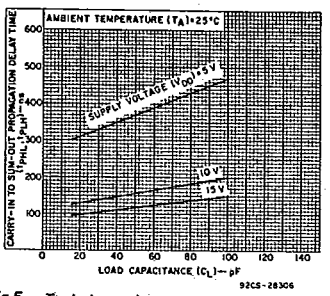


Fig.5 – Typical carry-in to sum-out propagation delay time vs. load capacitance.

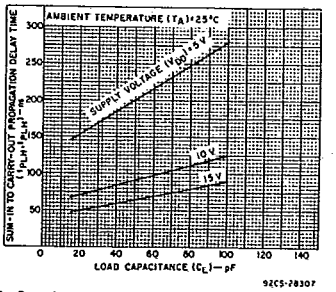


Fig.6 – Typical sum-in to carry-out propagation delay time vs. load capacitance.

3 COMMERCIAL CMOS HIGH VOLTAGE ICs

DYNAMIC ELECTRICAL CHARACTERISTICS
At T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200kΩ

CHARACTERISTIC	V_{DD} (V)	LIMITS		UNITS
		TYP.	MAX.	
Propagation Delay Time: t_{PHL}, t_{PLH} Sum In to Sum Out	5	400	800	ns
	10	160	320	
	15	115	230	
Carry In to Sum Out	5	370	740	ns
	10	155	310	
	15	115	230	
Sum In to Carry Out	5	200	400	ns
	10	90	180	
	15	65	130	
Carry In to Carry Out	5	100	200	ns
	10	50	100	
	15	40	80	
Transition Time: t_{THL}, t_{TLH}	5	100	200	ns
	10	50	100	
	15	40	80	
Input Capacitance, C_{IN}	–	5	7.5	pF

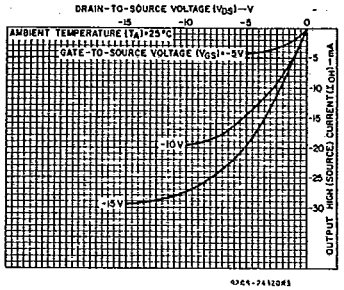


Fig.7 – Typical output high (source) current characteristics.

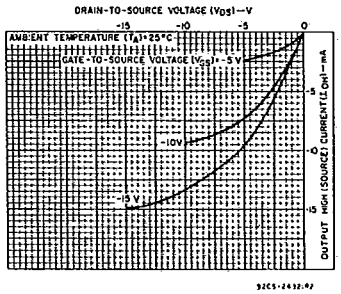


Fig.8 – Minimum output high (source) current characteristics.

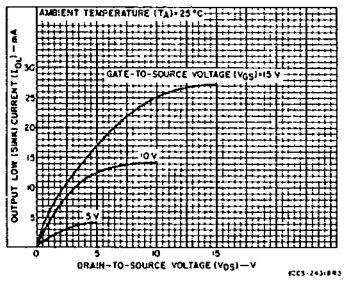


Fig.9 – Typical output low (sink) current characteristics.

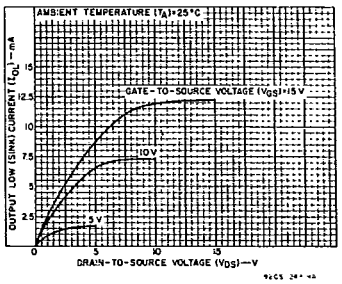


Fig.10 – Minimum output low (sink) current characteristics.

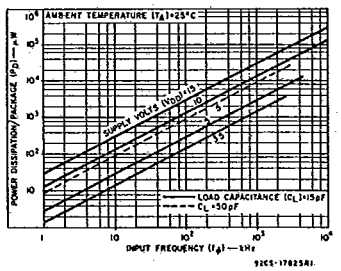


Fig.11 – Typical dissipation characteristics.

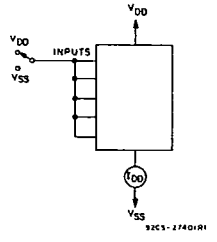


Fig.12 – Quiescent-device-current test circuit.

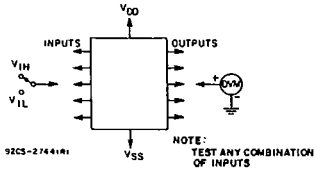


Fig.13 – Input-voltage test circuit.

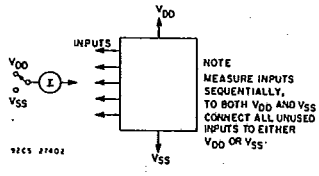
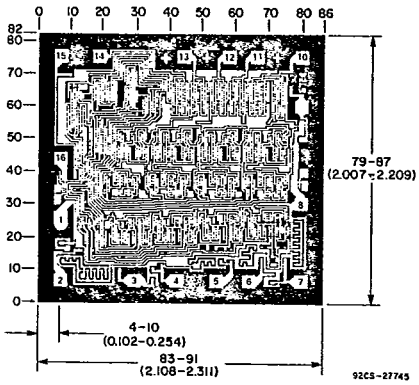


Fig.14 – Input current test circuit.

T-45-07



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

Dimensions and Pad Layout for CD4008BH